



DMT68M8LFV

60V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	9.5mΩ @ V _{GS} = 10V	54.1A
60V	13.3mΩ @ V _{GS} = 4.5V	45.7A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- **DC-DC** Converters
- **Power Management**

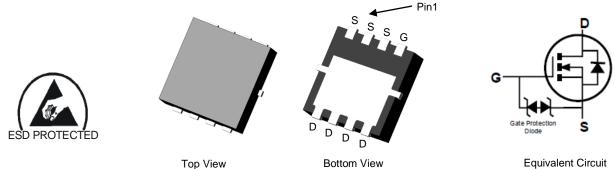
Features and Benefits

- 100% Unclamped Inductive Switching (UIS) Test in Production -Ensures More Reliable And Robust End Application
- Low RDS(ON) Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher **Density End Products**
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- **ESD** Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.072 grams (Approximate)

PowerDI3333-8 (Type UX)



Ordering Information (Note 4)

	Part Number	Case	Packaging		
	DMT68M8LFV-7	PowerDI3333-8 (Type UX)	2000/Tape & Reel		
DMT68M8LFV-13 PowerDI3333-8 (Type UX) 3000/Tape & Reel					
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS). 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.					

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



688= Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 18 = 2018) WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	60	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 6) V _{GS} = 10V	ID	54.1 43.3	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	210	А
Maximum Continuous Body Diode Forward Current (Note 6)		ls	50	А
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	210	А	
Avalanche Current, L = 0.1mH		IAS	28	А
Avalanche Energy, L = 0.1mH		E _{AS}	39	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	PD	2.7	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{ ext{ heta}JA}$	47	°C/W
Total Power Dissipation (Note 6) $T_{\rm C} = +25^{\circ}{\rm C}$		PD	41.7	W
Thermal Resistance, Junction to Case (Note 6)	R _θ JC	3	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C	

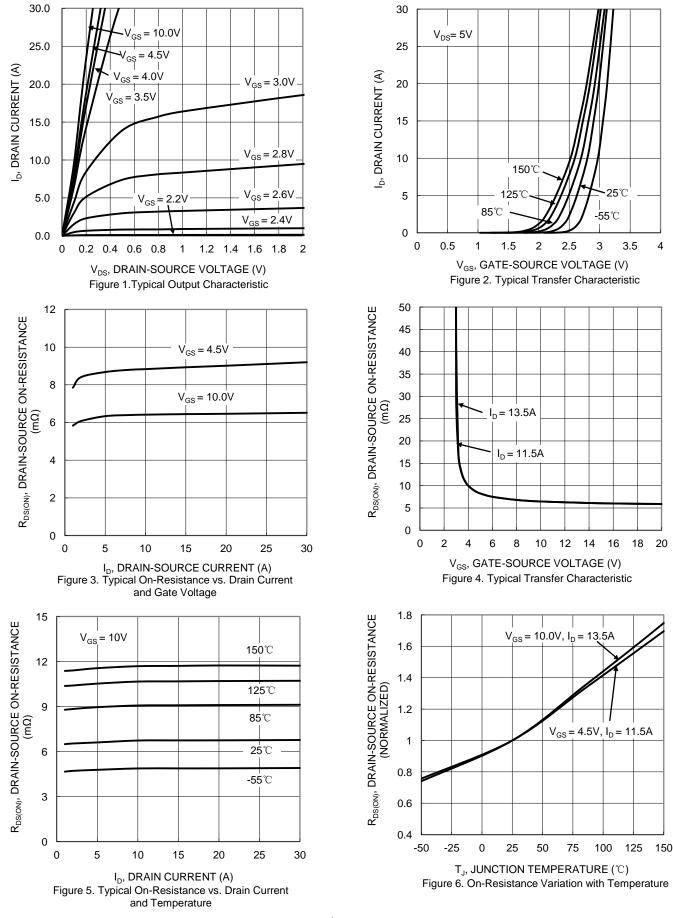
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	0,		. 76		•		
Drain-Source Breakdown Voltage	BV _{DSS}	60		_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}		_	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Deserve		6.6	9.5	mΩ	$V_{GS} = 10V, I_D = 13.5A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		9.1	13.3	11122	V _{GS} = 4.5V, I _D = 11.5A	
Diode Forward Voltage	V _{SD}		0.8	1.2	V	$V_{GS} = 0V, I_{S} = 13.5A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		2078	—	pF		
Output Capacitance	Coss		605	—	pF	[−] V _{DS} = 30V, V _{GS} = 0V, − f = 1MHz	
Reverse Transfer Capacitance	Crss		44	-	pF		
Gate Resistance	R _g		1.71	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg		30	—	nC		
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	14.4	-	nC	עם = 30V. א = 20A	
Gate-Source Charge	Q _{gs}	_	4.1		nC	$v_{DD} = 30v, I_D = 20A$	
Gate-Drain Charge	Q _{gd}	_	6.7	-	nC		
Turn-On Delay Time	t _{D(ON)}	_	5.2	_	ns		
Turn-On Rise Time	t _R	_	9.6	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	20.5	_	ns	$I_{D} = 20A, R_{g} = 3.3\Omega$	
Turn-Off Fall Time	t _F	_	8.9	_	ns		
Body Diode Reverse Recovery Time	t _{RR}	_	32.5	_	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	_	22.8	_	nC	— I _F = 20A, di/dt = 100A/μs	

 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad)
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing. Note:



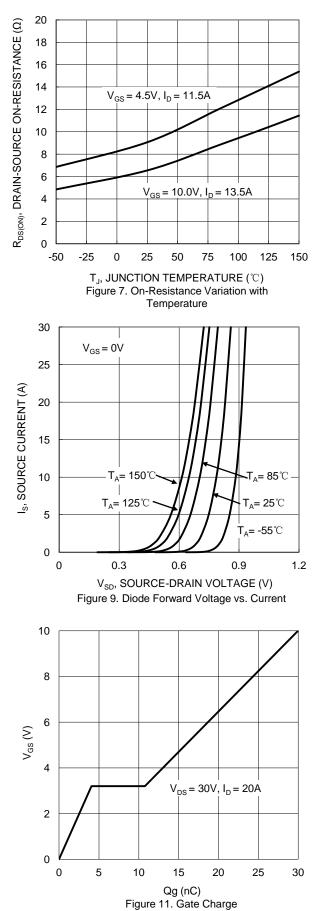
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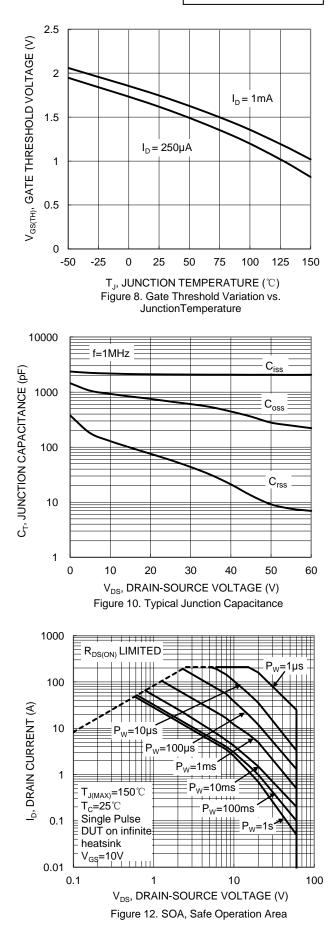


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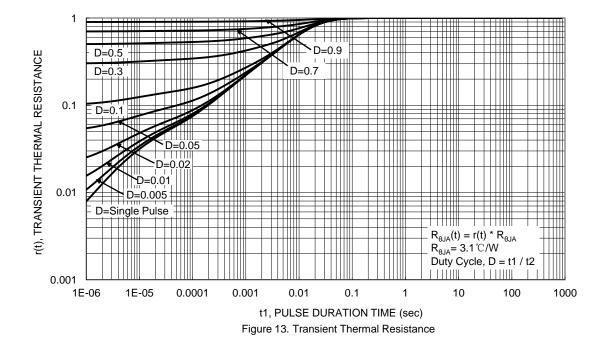
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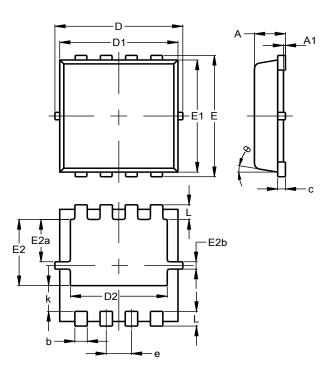




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)

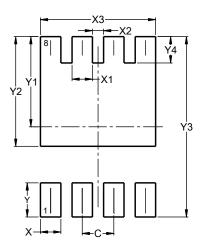


PowerDI3333-8 (Type UX)						
Dim	Min	Тур				
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.20 3.40 3.30				
D1	2.95	2.95 3.15 3.				
D2	2.30 2.70		2.50			
Е	3.20	3.40	3.30			
E1	2.95	2.95 3.15 3				
E2	1.60	1.60 2.00 1.8				
E2a	0.95	0.95 1.35 1.1				
E2b	0.10	0.10 0.30 0.20				
е	0.65 BSC					
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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